

**UHF power transistor**

**BLV99**

**Description:**

NPN silicon planar epitaxial transistor encapsulated in a 4-lead SOT172D envelope with a ceramic cap. It is designed primarily for use as a driver stage in base stations in the 900 MHz communications band. All leads are isolated from the mounting base.

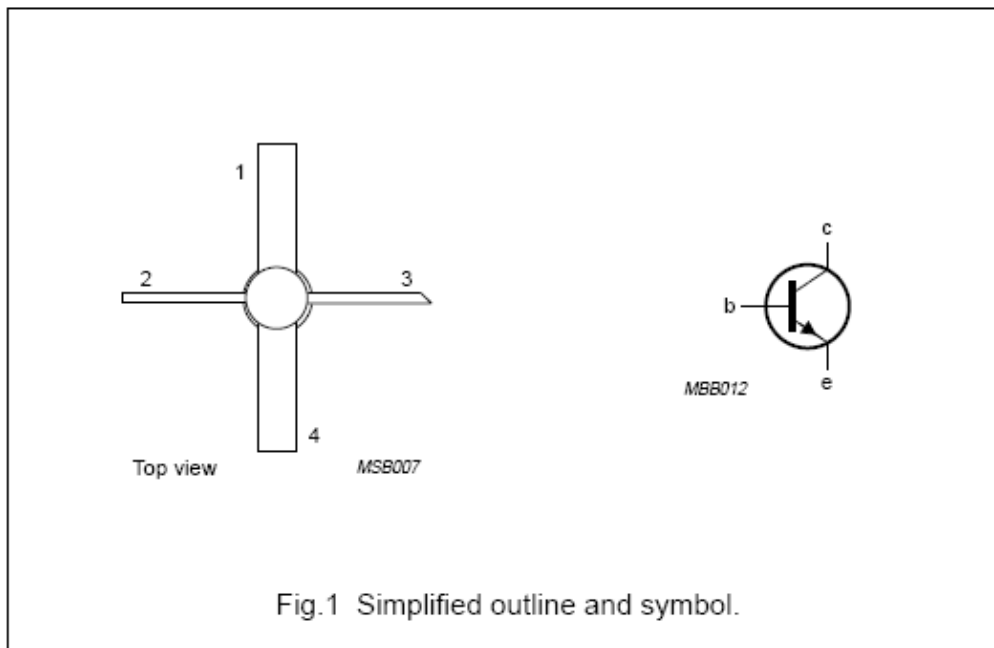
**Features:**

- \* Emitter-ballasting resistors for an optimum temperature profile
- \* Gold metallization ensures excellent reliability.

**Data:**

MODE OF OPERATION	f (MHz)	V <sub>CE</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	η <sub>c</sub> (%)
c.w. narrow band	900	24	2	> 8	> 55

**Drawings:**



PIN	DESCRIPTION
1	emitter
2	base
3	collector
4	emitter